

# P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
- 20	0.184 at V <sub>GS</sub> = - 4.5 V	- 0.94	4.23			
- 20	0.268 at V <sub>GS</sub> = - 2.5 V	- 0.78	4.20			

### **FEATURES**

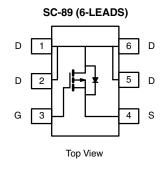
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>q</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

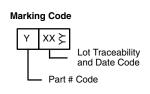


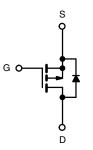
ROHS COMPLIANT HALOGEN FREE

### **APPLICATIONS**

• Load Switch for Portable Devices







Ordering Information: Si1069X-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 20	V		
Gate-Source Voltage		V <sub>GS</sub>	± 12	v		
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>A</sub> = 25 °C	1-	- 0.94 <sup>b, c</sup>			
Continuous Diam Current (1) = 150 C)	T <sub>A</sub> = 70 °C	I <sub>D</sub>	- 0.75 <sup>b, c</sup>	Α		
Pulsed Drain Current		I <sub>DM</sub>	- 8			
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 0.2 <sup>b, c</sup>			
Maniana Banas Bissis stand	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.236 <sup>b, c</sup>	w		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.151 <sup>b, c</sup>			
Operating Junction and Storage Temperature Ra	inge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
AA:' ht' t At-'ta h	t ≤ 5 s	D	440	530	°C/W	
Maximum Junction-to-Ambient <sup>a, b</sup>	Steady State	R <sub>thJA</sub>	540	650	C/VV	

### Notes:

- a. Based on  $T_A = 25$  °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.

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Parameter	Symbol Test Conditions		Min. Typ.		Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050A		- 16.7		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	l <sub>D</sub> = - 250 μA		2.95			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	I	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = \ge 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 8			Α	
5 . 6 . 6	_	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.94 A	0.153		0.184		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 0.78 A		0.218	0.268	Ω	
Forward Transconductance	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 0.94 A		4		S	
Dynamic <sup>b</sup>					•		
Input Capacitance	C <sub>iss</sub>			308		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		78			
Reverse Transfer Capacitance	C <sub>rss</sub>			59			
Total Cata Charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -0.94 \text{ A}$		4.57	6.86		
Total Gate Charge	$\mathcal{Q}_{g}$	Q <sub>g</sub>		4.23	6.35		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.94 \text{ A}$		0.71		nC	
Gate-Drain Charge	Q <sub>gd</sub>			1.67		1	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	9		13.5	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			19	28.5		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_{L} = 13.3 \Omega$		31	47	1	
Turn-Off DelayTime	t <sub>d(off)</sub>	$I_D \cong -0.75 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		23	34.5	ns	
Fall Time	t <sub>f</sub>			7	10.5	1	
Drain-Source Body Diode Characteris	stics					ı	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				8	Α	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 0.64 A		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			19	28.5	nC	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	1 _ 0 64 A dl/d+ 400 A/::-		6.65	10		
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = -0.64 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		7		ns	
Reverse Recovery Rise Time	t <sub>b</sub>	7		12		1	

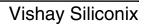
### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

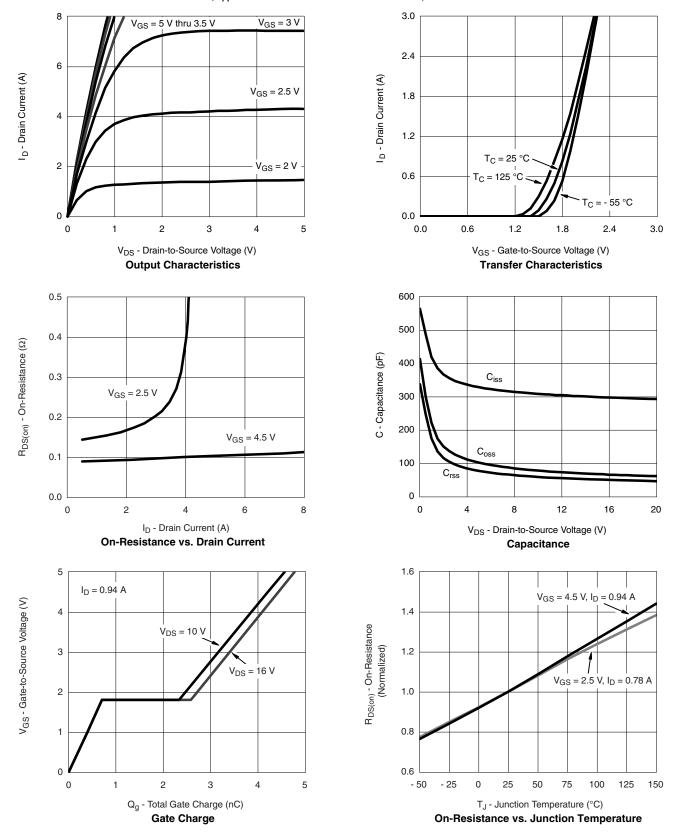
b. Guaranteed by design, not subject to production testing.







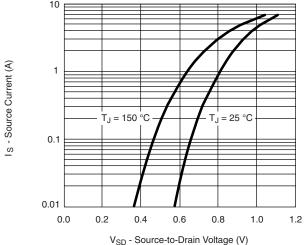
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



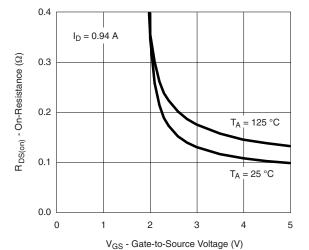
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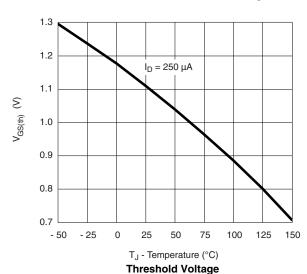
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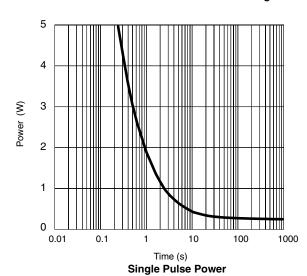


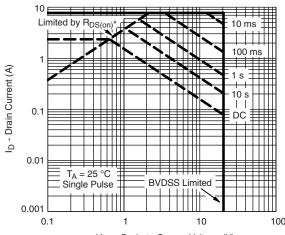
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage







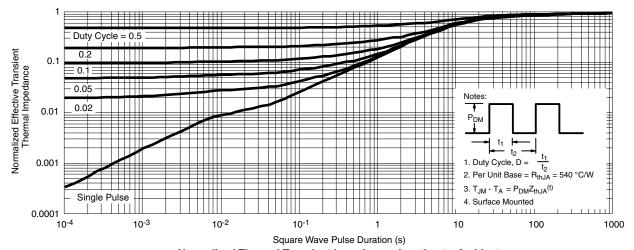
 $V_{DS} \mbox{ - Drain-to-Source Voltage (V)} \\ ^{\star} V_{GS} \mbox{ > minimum } V_{GS} \mbox{ at which } R_{DS(on)} \mbox{ is specified}$ 

Safe Operating Area, Junction-to-Ambient





## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



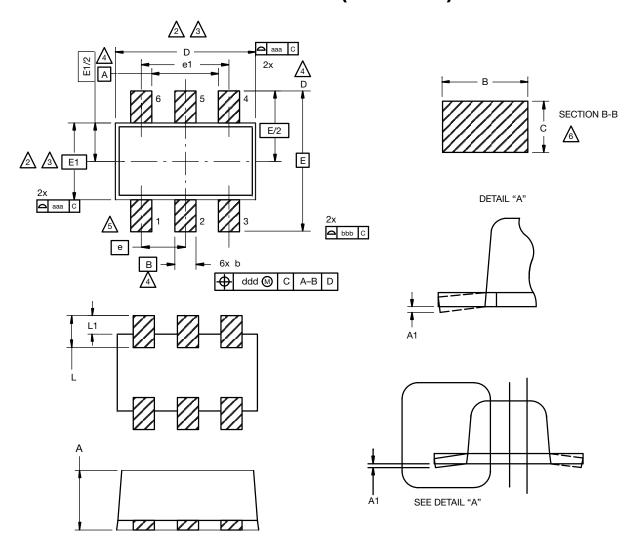
Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppq?70442">www.vishay.com/ppq?70442</a>.

Document Number: 70442 S19-0207-Rev. D, 04-Mar-2019



## **SC-89 6-Leads (SOT-563F)**



### Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

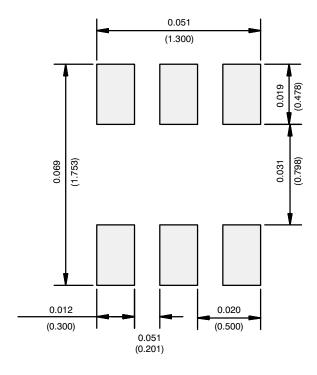
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS				
	MIN.	NOM.	MAX.		
Α	0.56	0.58	0.60		
A1	0	0.02	0.10		
b	0.15	0.22	0.30		
С	0.10	0.14	0.18		
D	1.50	1.60	1.70		
E	1.50	1.60	1.70		
E1	1.15	1.20	1.25		
е	0.45	0.50	0.55		
e1	0.95	1.00	1.05		
L	0.25	0.35	0.50		
L1	0.10	0.20	0.30		
C14-0439-Rev. C, 11-Aug-14 DWG: 5880					



### **RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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